

#4 IDS  
DRAFT  
2-20-01

Inventor: Charles H. Dennison

Title: Field Effect Transistors, Integrated Circuitry, Methods of Forming  
Field Effect Transistor Gates, and Methods of Forming Integrated  
Circuitry

Assignee: Micron Technology, Inc.

**INFORMATION DISCLOSURE STATEMENT****PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98**

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

With the exception of the patents listed hereinbelow, the references listed in the attached Form PTO-1449 were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation application of co-pending application Serial No. 09/138,150, filed August 21, 1998. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2).

Copies of the following U.S. patents are submitted herewith. Said patents were not submitted in the parent application:

4,884,123  
4,997,785  
5,282,972  
5,510,646  
5,576,579  
5,640,037  
5,641,708  
5,753,528  
5,776,823  
5,796,166

Citation of all references is respectfully requested.

Respectfully submitted,

Dated: 12-4-00

By:   
Mark S. Matkin  
Reg. No. 32,268